

Appl. No. 10/650,505  
Am(d)t. Dated June 6, 2006  
Reply to Office Action of March 9, 2006

Attorney Docket No. 81872.0051  
Customer No. 26021

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-12. (Canceled)

13. (Currently amended) A dry etching method ~~for forming fine textures on a surface of a substrate to be etched, said dry etching method~~ comprising:

placing a substrate to be etched on an RF electrode provided inside a chamber, directly or through a tray; and

covering said substrate to be etched with a plate~~[[,]]~~; and

forming fine fixtures on a surface of said substrate to be etched by a reactive ion etching method;

wherein said plate comprises an obstacle with a plurality of obstacle forming members that inhibit a part of gas and plasma from passing through said plate.

14. (Previously presented) The dry etching method according to Claim 13, wherein said substrate to be etched is made of silicon.

15. (Currently amended) The dry etching method according to Claim 13, wherein said plate covers said substrate to be etched while ~~securing~~ a distance of 5 mm to 30 mm is between the substrate and plate.

16-17. (Canceled)

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18. (Currently amended) A dry etching method, comprising:  
placing a substrate to be etched on an RF electrode provided inside a chamber, directly or through a tray; and  
covering said substrate to be etched with a plate provided with a number of opening portions[[],] ; and  
etching the substrate by a reactive ion etching method;  
wherein fine textures are formed on a surface of said substrate to be etched and said plate is cleaned on a surface side concurrently.

19. (Currently amended) The dry etching method according to Claim [[18]]  
20, wherein said dry etching method is a reactive ion etching method.

20. (Currently amended) The A dry etching method according to Claim 18, comprising:

placing a substrate to be etched on an RF electrode provided inside a chamber, directly or through a tray; and

covering said substrate to be etched with a plate provided with a number of opening portions;

wherein fine textures are formed on a surface of said substrate to be etched and said plate is cleaned on a surface side concurrently.

wherein a substrate to be etched next is placed inside a chamber, with said plate positioned such that a surface and a back surface are reversed after said plate is cleaned on the surface side, and fine textures are formed on a surface of said substrate to be etched next.

21-22. (Canceled)

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23. (Previously presented) The dry etching method according to Claim 13, wherein an opening portion is provided between neighboring obstacle forming members.

24. (Previously presented) The dry etching method according to Claim 23, wherein an open area ratio of said obstacle is 5 to 40%.

25. (Previously presented) The dry etching method according to Claim 13, wherein said obstacle forming members are a plurality of long members aligned with a clearance in between.

26. (Previously presented) The dry etching method according to Claim 25, wherein said long member is a bar-shaped or sheet member.

27. (Previously presented) The dry etching method according to Claim 13, wherein said obstacle forming member comprises a mesh woven by crossing said plurality of long members over and under with each other.

28. (Currently amended) The dry etching method according to Claim 13, wherein said obstacle comprises a plurality of obstacles of a ~~laminated~~ stacked structure.

29. (Currently amended) The dry etching method according to Claim 28, wherein said obstacle comprises a member formed by ~~laminating~~ stacking a plurality of long members aligned with a clearance in between, in different directions.

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30. (Previously presented) The dry etching method according to Claim 13, wherein said obstacle forming member is made of one kind or a combination of two or more kinds selected from a group consisting of materials (a), (b), and (c) as follows:

- (a) a glass-based material;
- (b) a metal material; and
- (c) a resin material.

31. (Previously presented) The dry etching method according to Claim 30, wherein said metal material is an aluminum-based material.

32. (Previously presented) The dry etching method according to Claim 18, wherein said plate is structured in such a manner that a surface and a back surface can be reversed.

33. (Previously presented) The dry etching method according to Claim 32, wherein the surface and the back surface of said plate are of substantially a same shape.

34. (Currently amended) A dry etching method for forming fine textures on a surface of a substrate to be etched, said dry etching method comprising:

placing a substrate to be etched on an RF electrode provided inside a chamber, directly or through a tray; and

covering said substrate to be etched with a plate comprising an obstacle that inhibits a part of a gas and plasma from passing through said plate[L]; and

etching the substrate by a reactive ion etching method;

wherein a member forming said obstacle is provided with a number of opening portions.

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35. (Previously presented) The dry etching method according to Claim 34, wherein an open area ratio of said obstacle is 5 to 40%.

36. (Previously presented) The dry etching method according to Claim 34, wherein said substrate to be etched is made of silicon.

37. (Currently amended) The dry etching method according to Claim 34, wherein said plate covers said substrate to be etched while securing a distance of 5 mm to 30 mm is between the substrate and plate.

38. (Canceled)

39. (Previously presented) The dry etching method according to Claim 34, wherein said obstacle is made of one kind or a combination of two or more kinds selected from a group consisting of materials (a), (b), and (c) as follows:

- (a) a glass-based material;
- (b) a metal material; and
- (c) a resin material.

40. (Previously presented) The dry etching method according to Claim 39, wherein said metal material is an aluminum-based material.